



DMN61D8L/LVT

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C, SOT23
60V	1.8Ω @ V _{GS} = 5V	470~ 4
000	2.4Ω @ V _{GS} = 3V	470mA

Description and Applications

DMN61D8L/LVT provides a single component solution for switching inductive loads such as relays, solenoids, and small DC motors in automotive applications, without the need of a freewheeling diode. DMN61D8L/LVT accepts logic level inputs, thus allowing it to be driven by logic gates, inverters, and microcontrollers. It is ideally suited for doors, windows, and antenna relay coils.



60V N-CHANNEL ENHANCEMENT MODE MOSFET

Features and Benefits

- Provides a more reliable and robust interface between sensitive logic and DC relay coils
- Replaces 3 to 4 discrete components enabling PCB footprint to be reduced
- Internal active clamp removes the need for external zener diode
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- The Automotive-Compliant Parts are Available Under Separate Datasheets (DMN61D8LQ and DMN61D8LVTQ)

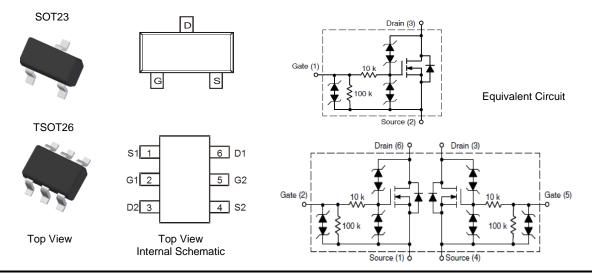
Mechanical Data

Case: SOT23

- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Alloy 42 Leadframe. (Lead-Free Plating). Solderable per MIL-STD-202, Method 208 (e3)
- Terminals Connections: See Diagram
- Weight: 0.008 grams (Approximate)

Case: TSOT26

- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.013 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging			
DMN61D8L-7	SOT23	3,000/Tape & Reel			
DMN61D8L-13	SOT23	10,000/Tape & Reel			
DMN61D8LVT-7 TSOT26 3,000/Tape & Reel					
DMN61D8LVT-13 TSOT26 10,000/Tape & Reel					
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

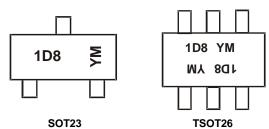
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information



 $\begin{array}{l} 1D8 = Product \ Type \ Marking \ Code \\ YM = Date \ Code \ Marking \\ Y \ or \ \overline{Y} = Year \ (ex: \ F= 2018) \\ M = Month \ (ex: \ 9 = September) \end{array}$

Date Code Key

Year	2014	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	В	С	D	E	F	G	Н		J	K	L	М	N
Mon	th	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Cod	le	1	2	3	4	5	6	7	8	9	0	Ν	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) SOT23	Steady State	T _A = +25°C T _A = +70°C	ID	470 370	mA
Continuous Drain Current (Note 6) TSOT26	Steady State	T _A = +25°C T _A = +70°C	ID	630 500	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	0.5	А
Single Pulse Drain-to-Source Avalanche Energy (for relay coils/inductive loads of 80Ω or higher) (TJ initial = +85°C)			Ez	200	mJ
Peak Power Dissipation, Drain-to-Source (non-repetitive current square pulse 1.0ms duration) (T _J initial = +85°C)			Ррк	20	W
Load Dump Pulse, Drain-to-Source, $R_{SOURCE} = 0.5\Omega$, t = 300ms) (for relay coils/inductive loads of 80 Ω or higher) (T _J Initial = +85°C)			E _{LD1}	60	V
Inductive Switching Transient 1, Drain-to-Source (Waveform: $R_{SOURCE} = 10\Omega$, t = 2.0ms) (for relay coils/inductive loads of 80 Ω or higher) (T _J Initial = +85°C)			E _{LD2}	100	V
Inductive Switching Transient 2, Drain-to-Source (Waveform: $R_{SOURCE} = 4.0\Omega$, t = 50µs) (for relay coils/inductive loads of 80Ω or higher) (T _J Initial = +85°C)			ELD3	300	V
Reverse Battery, 10 Minutes (Drain-to-Source) (for relay coils/inductive loads of 80Ω or higher)			Rev-Bat	-14	V
Dual Voltage Jump Start, 10 Minutes (Drain-to-Sou	rce)		Dual-Volt	28	V
ESD Human Body Model (HBM)			ESD	4,000	V



Thermal Characteristics (SOT23) (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	390	mW	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	321	°C/W
Total Power Dissipation (Note 6)		PD	610	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	208	°C/W
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C

Thermal Characteristics (TSOT26) (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		PD	820	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R_{\thetaJA}	154	°C/W
Total Power Dissipation (Note 6)		PD	1090	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R_{\thetaJA}	116	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

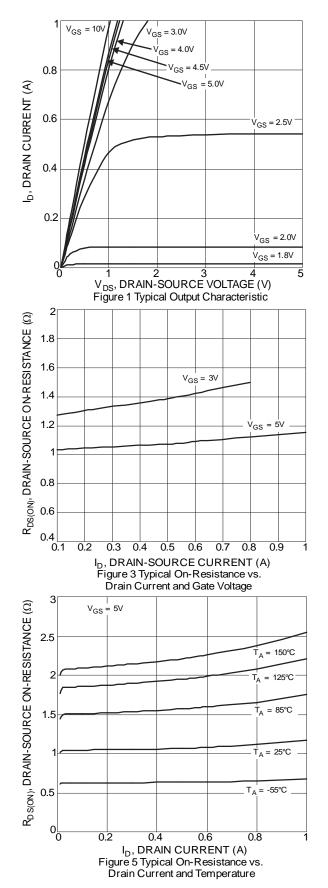
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			•			•	
Drain-Source Breakdown Voltage	BV _{DSS}	60	_	_	V	$V_{GS} = 0V, I_D = 10mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	50 0.5	μA	$V_{DS} = 60V, V_{GS} = 0V$ $V_{DS} = 12V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±90 ±60	μA	$V_{GS} = \pm 5V, V_{DS} = 0V$ $V_{GS} = \pm 3V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.3	_	2.0	V	$V_{DS} = V_{GS}, I_D = 1mA$	
Static Drain-Source On-Resistance	Deserve		1.1	1.8	Ω	$V_{GS} = 5V, I_D = 0.15A$	
Static Drain-Source On-Resistance	R _{DS(ON)}		1.4	2.4	12	$V_{GS} = 3V, I_D = 0.15A$	
Forward Transfer Admittance	Y _{fs}	80	_	_	ms	V _{DS} =12V, I _D = 0.15A	
Diode Forward Voltage	V _{SD}	_	_	1.2	V	V _{GS} = 0V, I _S = 0.15A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	12.9		pF		
Output Capacitance	C _{oss}	_	17		pF	V _{DS} = 12V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	0.84	_	pF	1 - 1.000112	
Total Gate Charge	Qg	_	0.74	_	nC		
Gate-Source Charge	Q _{gs}	_	0.19	_	nC	V _{GS} = 5V, V _{DS} = 12V, I _D =150mA	
Gate-Drain Charge	Q _{gd}	_	0.16	_	nC	$I_D = 150 \text{mA}$	
Turn-On Delay Time	t _{D(ON)}		131		ns		
Turn-On Rise Time	t _R		301		ns		
Turn-Off Delay Time	t _{D(OFF)}		582	_	ns	$V_{DD} = 12V, V_{GS} = 5V$	
Turn-Off Fall Time	t _F	_	440	_	ns		

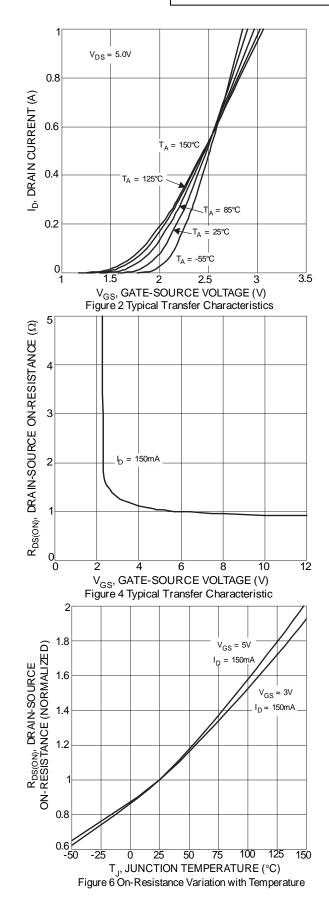
5. Device mounted on FR-4 PCB, with minimum recommended pad layout. Notes:

Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. copper, single sided.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

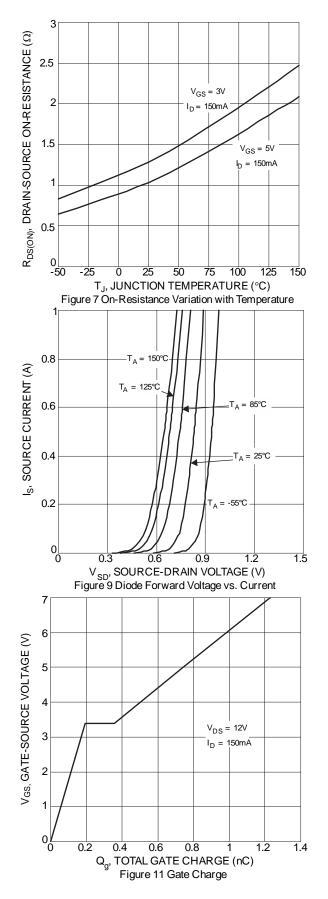


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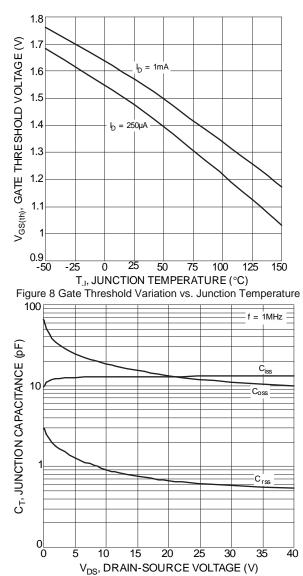
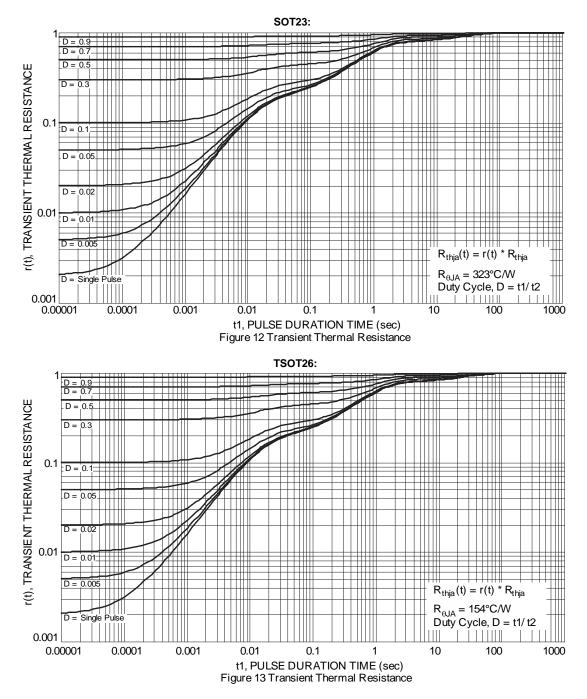


Figure 10 Typical Junction Capacitance



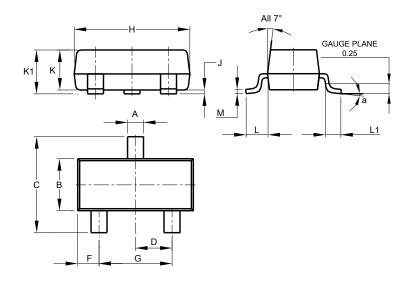




Package Outline Dimensions

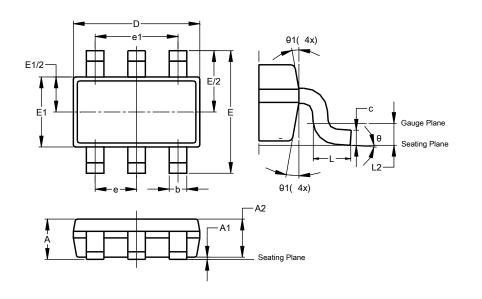
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



	SO	T23	
Dim	Min	Max	Тур
Α	0.37	0.51	0.40
в	1.20	1.40	1.30
c	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
н	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
Μ	0.085	0.150	0.110
а	0°	8°	
All	Dimens	ions in	mm

TSOT26



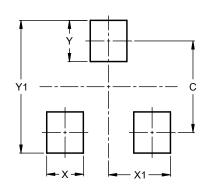
	TS	OT26			
Dim	Min	Max	Тур		
Α	-	1.00	-		
A1	0.010	0.100	-		
A2	0.840	0.900	-		
D	2.800	3.000	2.900		
Е	2.800 BSC				
E1	1.500	1.700	1.600		
q	0.300	0.450	-		
С	0.120	0.200	-		
e	0.950 BSC				
e1	1	.900 BS	C		
L	0.30	0.50	-		
L2	0	.250 BS	C		
θ	0°	8°	4°		
θ1	4°	12°	-		
A	II Dimen	sions in	mm		



Suggested Pad Layout

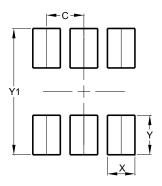
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SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

TSOT26



Dimensions	Value (in mm)
С	0.950
Х	0.700
Y	1.000
Y1	3.199



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